

## **FJD3076**

### **Power Amplifier Applications**

• Low Collector-Emitter Saturation Voltage



1. Base 2. Collector 3. Emitter

## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	32	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1	W
	Collector Dissipation (T <sub>C</sub> =25°C)	10	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	32			V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 50\mu A$	40			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 50\mu A$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 20V, I_{E} = 0$			1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 3V, I_{C} = 0.5A$	130		390	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 0.2A$		0.5	0.8	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 5V, I_{E} = -0.5A,$ f = 100MHz		100		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V$ , $I_E = 0A$ , $f = 1MHz$		50		pF

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# **Typical Characteristics**

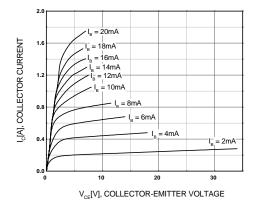


Figure 1. Static Characteristic

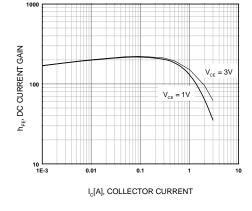


Figure 2. DC Current Gain

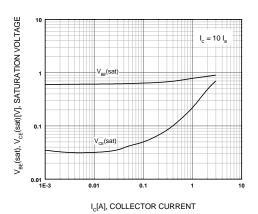


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

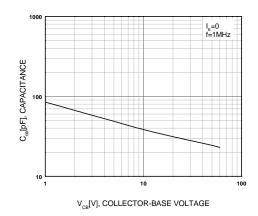


Figure 4. Collector Output Capacitance

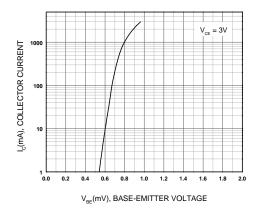


Figure 5. Base-Emitter On Voltage

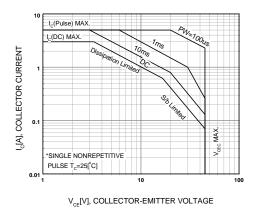
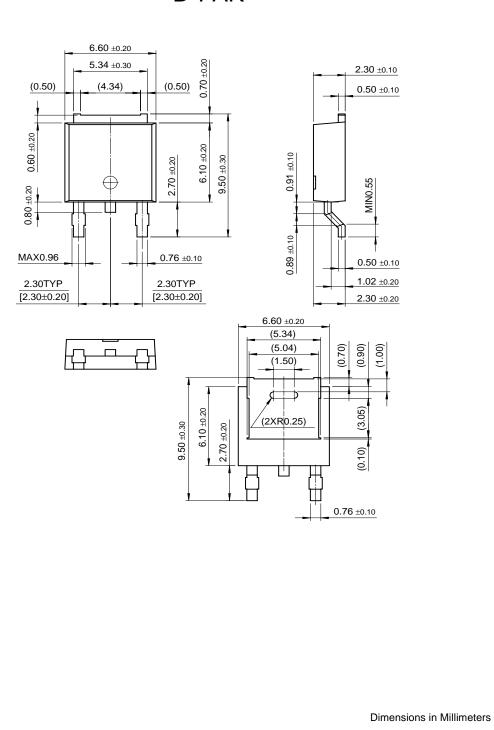


Figure 6. Safe Operating Area

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# **Package Demensions**

# D-PAK



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